

Abdallah Ougazzaden

List of Publications by Year in Descending Order

Source: <https://exaly.com/author-pdf/7161787/abdallah-ougazzaden-publications-by-year.pdf>

Version: 2024-04-28

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

251
papers

3,805
citations

31
h-index

47
g-index

275
ext. papers

4,491
ext. citations

2.8
avg, IF

4.65
L-index

#	Paper	IF	Citations
251	A cost-effective technology to improve power performance of nanoribbons GaN HEMTs. <i>Applied Physics Letters</i> , 2022 , 120, 042102	3.4	0
250	Influence of Sapphire Substrate Orientation on the van der Waals Epitaxy of III-Nitrides on 2D Hexagonal Boron Nitride: Implication for Optoelectronic Devices. <i>ACS Applied Nano Materials</i> , 2022 , 5, 791-800	5.6	0
249	Natural Boron and B-Enriched Hexagonal Boron Nitride for High-Sensitivity Self-Biased Metal-Semiconductor-Metal Neutron Detectors.. <i>ACS Omega</i> , 2022 , 7, 804-809	3.9	0
248	Monolithic Free-Standing Large-Area Vertical III-N Light-Emitting Diode Arrays by One-Step h-BN-Based Thermomechanical Self-Lift-Off and Transfer. <i>ACS Applied Electronic Materials</i> , 2021 , 3, 2614-2621	4.2	3
247	MOVPE of GaN-based mixed dimensional heterostructures on wafer-scale layered 2D hexagonal boron nitride: A key enabler of III-nitride flexible optoelectronics. <i>APL Materials</i> , 2021 , 9, 061101	5.7	2
246	Towards P-Type Conduction in Hexagonal Boron Nitride: Doping Study and Electrical Measurements Analysis of hBN/AlGaN Heterojunctions. <i>Nanomaterials</i> , 2021 , 11,	5.4	4
245	Single crystalline boron rich B(Al)N alloys grown by MOVPE. <i>Applied Physics Letters</i> , 2020 , 116, 042101	3.4	7
244	The 2020 UV emitter roadmap. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 503001	3	123
243	Control of the Mechanical Adhesion of III-V Materials Grown on Layered h-BN. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 55460-55466	9.5	4
242	Highly Ordered Boron Nitride/Epigraphene Epitaxial Films on Silicon Carbide by Lateral Epitaxial Deposition. <i>ACS Nano</i> , 2020 , 14, 12962-12971	16.7	5
241	Effectiveness of selective area growth using van der Waals h-BN layer for crack-free transfer of large-size III-N devices onto arbitrary substrates. <i>Scientific Reports</i> , 2020 , 10, 21709	4.9	6
240	Light-Emitting Diodes: Large-Area van der Waals Epitaxial Growth of Vertical III-Nitride Nanodevice Structures on Layered Boron Nitride (Adv. Mater. Interfaces 16/2019). <i>Advanced Materials Interfaces</i> , 2019 , 6, 1970102	4.6	0
239	Nanopyramid-based absorber to boost the efficiency of InGaN solar cells. <i>Solar Energy</i> , 2019 , 190, 93-103	3.8	2
238	Large-Area van der Waals Epitaxial Growth of Vertical III-Nitride Nanodevice Structures on Layered Boron Nitride. <i>Advanced Materials Interfaces</i> , 2019 , 6, 1900207	4.6	9
237	Novel Scalable Transfer Approach for Discrete III-Nitride Devices Using Wafer-Scale Patterned h-BN/Sapphire Substrate for Pick-and-Place Applications. <i>Advanced Materials Technologies</i> , 2019 , 4, 1900164	6.8	8
236	Heterogeneous Integration: Novel Scalable Transfer Approach for Discrete III-Nitride Devices Using Wafer-Scale Patterned h-BN/Sapphire Substrate for Pick-and-Place Applications (Adv. Mater. Technol. 10/2019). <i>Advanced Materials Technologies</i> , 2019 , 4, 1970057	6.8	0
235	Sensors based on AlGaIn/GaN HEMT for fast H ₂ and O ₂ detection and measurement at high temperature 2019 ,		1

234	Wafer-scale MOVPE growth and characterization of highly ordered h-BN on patterned sapphire substrates. <i>Journal of Crystal Growth</i> , 2019 , 509, 40-43	1.6	9
233	MOVPE van der Waals epitaxial growth of AlGaN/AlGaN multiple quantum well structures with deep UV emission on large scale 2D h-BN buffered sapphire substrates. <i>Journal of Crystal Growth</i> , 2019 , 507, 352-356	1.6	5
232	Exfoliation of AlN film using two-dimensional multilayer hexagonal BN for deep-ultraviolet light-emitting diodes. <i>Applied Physics Express</i> , 2019 , 12, 015505	2.4	11
231	Modeling, design, fabrication and experimentation of a GaN-based, ⁶³ Ni betavoltaic battery. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 035101	3	15
230	Heterogeneous Integration of Thin-Film InGaN-Based Solar Cells on Foreign Substrates with Enhanced Performance. <i>ACS Photonics</i> , 2018 , 5, 3003-3008	6.3	15
229	Polarity governs atomic interaction through two-dimensional materials. <i>Nature Materials</i> , 2018 , 17, 999-1004	10.4	107
228	Controlled crack propagation for atomic precision handling of wafer-scale two-dimensional materials. <i>Science</i> , 2018 , 362, 665-670	33.3	133
227	Investigation of p-contact performance for indium rich InGaN based light emitting diodes and solar cells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600496	1.6	
226	InGaN/InGaN multiple-quantum-well grown on InGaN/GaN semi-bulk buffer for blue to cyan emission with improved optical emission and efficiency droop. <i>Superlattices and Microstructures</i> , 2017 , 104, 291-297	2.8	13
225	Nanoselective area growth of defect-free thick indium-rich InGaN nanostructures on sacrificial ZnO templates. <i>Nanotechnology</i> , 2017 , 28, 195304	3.4	1
224	Flexible metal-semiconductor-metal device prototype on wafer-scale thick boron nitride layers grown by MOVPE. <i>Scientific Reports</i> , 2017 , 7, 786	4.9	35
223	Evidence of minority carrier traps contribution in deep level transient spectroscopy measurement in n-GaN Schottky diode. <i>Superlattices and Microstructures</i> , 2017 , 101, 529-536	2.8	2
222	Influence of barrier layer indium on efficiency and wavelength of InGaN multiple quantum well (MQW) with and without semi-bulk InGaN buffer for blue to green regime emission. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600868	1.6	3
221	Optimization of semibulk InGaN-based solar cell using realistic modeling. <i>Solar Energy</i> , 2017 , 157, 687-693	6.8	18
220	Emission wavelength red-shift by using semi-bulk InGaN buffer layer in InGaN/InGaN multiple-quantum-well. <i>Superlattices and Microstructures</i> , 2017 , 112, 279-286	2.8	5
219	Dc and ac electrical response of MOCVD grown GaN in p-i-n structure, assessed through I _V and admittance measurement. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 505109	3	2
218	Gas sensors boosted by two-dimensional h-BN enabled transfer on thin substrate foils: towards wearable and portable applications. <i>Scientific Reports</i> , 2017 , 7, 15212	4.9	41
217	Improving InGaN heterojunction solar cells efficiency using a semibulk absorber. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 159, 405-411	6.4	17

216	Mask effect in nano-selective- area-growth by MOCVD on thickness enhancement, indium incorporation, and emission of InGaN nanostructures on AlN-buffered Si(111) substrates. <i>Optical Materials Express</i> , 2017 , 7, 376	2.6	3
215	Epitaxial Graphene on SiC: 2D Sheets, Selective Growth, and Nanoribbons 2017 , 181-204		0
214	High-efficiency indium gallium nitride/Si tandem photovoltaic solar cells modeling using indium gallium nitride semibulk material: monolithic integration versus 4-terminal tandem cells. <i>Progress in Photovoltaics: Research and Applications</i> , 2016 , 24, 1436-1447	6.8	7
213	Experimental Study and Device Design of NO, NO ₂ , and NH ₃ Gas Detection for a Wide Dynamic and Large Temperature Range Using Pt/AlGaN/GaN HEMT. <i>IEEE Sensors Journal</i> , 2016 , 16, 6828-6838	4	24
212	Wafer-scale epitaxial lift-off of optoelectronic grade GaN from a GaN substrate using a sacrificial ZnO interlayer. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 315105	3	12
211	Chemical lift-off and direct wafer bonding of GaN/InGaN PIN structures grown on ZnO. <i>Journal of Crystal Growth</i> , 2016 , 435, 105-109	1.6	2
210	Investigation of the Performance of HEMT-Based NO, NO ₂ and NH ₃ Exhaust Gas Sensors for Automotive Antipollution Systems. <i>Sensors</i> , 2016 , 16, 273	3.8	44
209	Nanoselective area growth of GaN by metalorganic vapor phase epitaxy on 4H-SiC using epitaxial graphene as a mask. <i>Applied Physics Letters</i> , 2016 , 108, 103105	3.4	9
208	Wafer-scale controlled exfoliation of metal organic vapor phase epitaxy grown InGaN/GaN multi quantum well structures using low-tack two-dimensional layered h-BN. <i>Applied Physics Letters</i> , 2016 , 108, 171106	3.4	56
207	Role of V-pits in the performance improvement of InGaN solar cells. <i>Applied Physics Letters</i> , 2016 , 109, 133507	3.4	6
206	Single-crystal nanopyramidal BGaN by nanoselective area growth on AlN/Si(111) and GaN templates. <i>Nanotechnology</i> , 2016 , 27, 115602	3.4	2
205	Large-Area Two-Dimensional Layered Hexagonal Boron Nitride Grown on Sapphire by Metalorganic Vapor Phase Epitaxy. <i>Crystal Growth and Design</i> , 2016 , 16, 3409-3415	3.5	81
204	Core-shell GaN/ZnO moth-eye nanostructure arrays grown on a-SiO ₂ /Si (1 1 1) as a basis for improved InGaN-based photovoltaics and LEDs. <i>Photonics and Nanostructures - Fundamentals and Applications</i> , 2015 , 15, 53-58	2.6	3
203	Scalable control of graphene growth on 4H-SiC C-face using decomposing silicon nitride masks. <i>Journal Physics D: Applied Physics</i> , 2015 , 48, 152001	3	5
202	AlGaN-based MQWs grown on a thick relaxed AlGaN buffer on AlN templates emitting at 285 nm. <i>Optical Materials Express</i> , 2015 , 5, 380	2.6	26
201	Structural and optical investigations of AlGaN MQWs grown on a relaxed AlGaN buffer on AlN templates for emission at 280 nm. <i>Journal of Crystal Growth</i> , 2015 , 432, 37-44	1.6	5
200	Highly sensitive detection of NO ₂ gas using BGaN/GaN superlattice-based double Schottky junction sensors. <i>Applied Physics Letters</i> , 2015 , 106, 243504	3.4	26
199	Model of Ni-63 battery with realistic PIN structure. <i>Journal of Applied Physics</i> , 2015 , 118, 105101	2.5	20

198	Nanoselective area growth and characterization of dislocation-free InGaN nanopyramids on AlN buffered Si(111) templates. <i>Applied Physics Letters</i> , 2015 , 107, 113105	3.4	13
197	High quality thick InGaN nanostructures grown by nanoselective area growth for new generation photovoltaic devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 740-744	1.6	7
196	BAlN thin layers for deep UV applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 745-750	1.6	30
195	Analysis of Deep Level Defects in GaN p-i-n Diodes after Beta Particle Irradiation. <i>Electronics (Switzerland)</i> , 2015 , 4, 1090-1100	2.6	7
194	Microstructural and electrical investigation of Pd/Au ohmic contact on p-GaN. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 010603	1.3	12
193	MOVPE grown periodic AlN/BAlN heterostructure with high boron content. <i>Journal of Crystal Growth</i> , 2015 , 414, 119-122	1.6	30
192	Role of compositional fluctuations and their suppression on the strain and luminescence of InGaN alloys. <i>Journal of Applied Physics</i> , 2015 , 117, 055705	2.5	19
191	On the elastic field and image force of dislocations in anisotropic solids and its application to GaN nanostructures. <i>Philosophical Magazine</i> , 2014 , 94, 1235-1248	1.6	
190	High performance TiN gate contact on AlGaIn/GaN transistor using a mechanically strain induced P-doping. <i>Applied Physics Letters</i> , 2014 , 104, 233506	3.4	10
189	Bandgap energy bowing parameter of strained and relaxed InGaIn layers. <i>Optical Materials Express</i> , 2014 , 4, 1030	2.6	63
188	Nanoscale selective area growth of thick, dense, uniform, In-rich, InGaIn nanostructure arrays on GaN/sapphire template. <i>Journal of Applied Physics</i> , 2014 , 116, 163105	2.5	15
187	Novel method for reclaim/reuse of bulk GaN substrates using sacrificial ZnO release layers 2014 ,		1
186	Contribution to solar concentrators design for photovoltaic application 2014 ,		2
185	Structural and compositional characterization of MOVPE GaN thin films transferred from sapphire to glass substrates using chemical lift-off and room temperature direct wafer bonding and GaN wafer scale MOVPE growth on ZnO-buffered sapphire. <i>Journal of Crystal Growth</i> , 2013 , 370, 63-67	1.6	42
184	Multilayered InGaIn/GaN structure vs. single InGaIn layer for solar cell applications: A comparative study. <i>Acta Materialia</i> , 2013 , 61, 6587-6596	8.4	35
183	Polarization-Induced Electric Fields Make Robust n-GaN/i-InGaIn/p-GaN Solar Cells. <i>IEEE Electron Device Letters</i> , 2013 , 34, 363-365	4.4	6
182	Analytical formulations of image forces on dislocations with surface stress in nanowires and nanorods. <i>International Journal of Solids and Structures</i> , 2013 , 50, 4341-4348	3.1	11
181	Nondestructive mapping of chemical composition and structural qualities of group III-nitride nanowires using submicron beam synchrotron-based X-ray diffraction. <i>Thin Solid Films</i> , 2013 , 541, 46-50	2.2	2

180	Analytical close-form solutions to the elastic fields of solids with dislocations and surface stress. <i>Philosophical Magazine</i> , 2013 , 93, 2497-2513	1.6	6
179	Suppression of crack generation in AlGaIn/GaN distributed Bragg reflectors grown by MOVPE. <i>Journal of Crystal Growth</i> , 2013 , 370, 12-15	1.6	12
178	Modeling of polarization effects on n-GaN/i-InGaIn/p-GaN solar cells with ultrathin GaN interlayers. <i>Optical and Quantum Electronics</i> , 2013 , 45, 681-686	2.4	2
177	Semibulk InGaIn: A novel approach for thick, single phase, epitaxial InGaIn layers grown by MOVPE. <i>Journal of Crystal Growth</i> , 2013 , 370, 57-62	1.6	41
176	Theoretical analysis of the influence of defect parameters on photovoltaic performances of composition graded InGaIn solar cells. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2013 , 178, 142-148	3.1	14
175	Characteristics of the surface microstructures in thick InGaIn layers on GaN. <i>Optical Materials Express</i> , 2013 , 3, 1111	2.6	20
174	Design, Fabrication, and Characterization of Near-Milliwatt-Power RCLEDs Emitting at 390 nm. <i>IEEE Photonics Journal</i> , 2013 , 5, 8400709-8400709	1.8	12
173	Comparison of chemical and laser lift-off for the transfer of InGaIn-based p-i-n junctions from sapphire to glass substrates 2013 ,		3
172	Growth of InGaIn/ZnO nanostructures on Si(111), c-Al ₂ O ₃ , ZnO and steel substrates by pulsed laser deposition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1317-1321		5
171	Dual-purpose B _{0.5} Ga _{0.5} In layers on performance of nitride-based high electron mobility transistors. <i>Applied Physics Letters</i> , 2012 , 100, 243503	3.4	24
170	A study of B _{0.5} Ga _{0.5} In back-barriers for AlGaIn/GaN HEMTs. <i>EPJ Applied Physics</i> , 2012 , 60, 30101	1.1	7
169	Interface state effects in GaN Schottky diodes. <i>Thin Solid Films</i> , 2012 , 522, 345-351	2.2	22
168	Finite element modeling of dislocation in solids and its applications to the analysis of GaN nanostructures. <i>Computational Materials Science</i> , 2012 , 58, 154-161	3.2	9
167	Nanometer-scale, quantitative composition mappings of InGaIn layers from a combination of scanning transmission electron microscopy and energy dispersive x-ray spectroscopy. <i>Nanotechnology</i> , 2012 , 23, 455707	3.4	27
166	Investigation of a relaxation mechanism specific to InGaIn for improved MOVPE growth of nitride solar cell materials. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 25-28	1.6	21
165	Novel process for direct bonding of GaN onto glass substrates using sacrificial ZnO template layers to chemically lift-off GaN from c-sapphire 2012 ,		4
164	Mechanism of Ohmic Cr/Ni/Au contact formation on p-GaN. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 022205	1.3	2
163	Distributed Bragg reflectors based on diluted boron-based BAlN alloys for deep ultraviolet optoelectronic applications. <i>Applied Physics Letters</i> , 2012 , 100, 051101	3.4	39

162	Tuning of internal gain, dark current and cutoff wavelength of UV photodetectors using quasi-alloy of B _{GaN} -GaN and B _{GaN} -AlN superlattices 2012 ,		7
161	Solar blind metal-semiconductor-metal ultraviolet photodetectors using quasi-alloy of B _{GaN} /GaN superlattices. <i>Applied Physics Letters</i> , 2011 , 99, 221101	3-4	33
160	New generation of Distributed Bragg Reflectors based on BAlN/AlN structures for deep UV-optoelectronic applications 2011 ,		1
159	Deep structural analysis of novel B _{GaN} material layers grown by MOVPE. <i>Journal of Crystal Growth</i> , 2011 , 315, 288-291	1.6	26
158	Structural and optical properties of nanodots, nanowires, and multi-quantum wells of III-nitride grown by MOVPE nano-selective area growth. <i>Journal of Crystal Growth</i> , 2011 , 315, 160-163	1.6	28
157	Blue-violet boron-based Distributed Bragg Reflectors for VCSEL application. <i>Journal of Crystal Growth</i> , 2011 , 315, 283-287	1.6	13
156	Link between crystal quality and electrical properties of metalorganic vapour phase epitaxy In _x Ga _{1-x} N thin films. <i>Applied Physics Letters</i> , 2011 , 99, 062113	3-4	4
155	Application of dilute boron B(Al,In,Ga)N alloys for UV light sources 2011 ,		3
154	Design, fabrication and physical analysis of TiN/AlN deep UV photodiodes. <i>Journal Physics D: Applied Physics</i> , 2010 , 43, 465104	3	12
153	Asymmetrical design for non-relaxed near-UV AlGa _N /Ga _N distributed Bragg reflectors 2010 ,		1
152	Epitaxial MOVPE growth of highly c-axis oriented InGa _N /Ga _N films on ZnO-buffered Si (111) substrates 2010 ,		2
151	Metal-organic vapour phase epitaxy of BInGa _N quaternary alloys and characterization of boron content. <i>Journal of Crystal Growth</i> , 2010 , 312, 641-644	1.6	14
150	Submicron beam X-ray diffraction of nanoheteroepitaxially grown GaN: Experimental challenges and calibration procedures. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2010 , 268, 320-324	1.2	4
149	Microstructural compositional, and optical characterization of GaN grown by metal organic vapor phase epitaxy on ZnO epilayers. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 1655		5
148	Selective growth of GaN nanodots and nanostripes on 6H-SiC substrates by metal organic vapor phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S510-S513		3
147	Electrical and structural characterizations of B _{GaN} thin films grown by metal-organic vapor-phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S1029-S1032		20
146	Mask pattern interference in AlGaInAs selective area metal-organic vapor-phase epitaxy: Experimental and modeling analysis. <i>Journal of Applied Physics</i> , 2008 , 103, 113113	2.5	15
145	Bandgap bowing in B _{GaN} thin films. <i>Applied Physics Letters</i> , 2008 , 93, 083118	3-4	42

144	Structural and morphological studies of GaN thin films grown on different oriented LiNbO ₃ substrates by MOVPE. <i>EPJ Applied Physics</i> , 2008 , 43, 295-299	1.1	3
143	New approach of Nano-Selective Area Growth (NSAG) for a precise control of GaN nanodots grown by MOVPE. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008 , 147, 114-117	3.1	8
142	GaN thin films on z- and x-cut LiNbO ₃ substrates by MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1565-1567		9
141	Raman scattering study of B _x Ga _{1-x} N growth on AlN template substrate. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 3051-3053		
140	Phonons in B _x Ga _{1-x} N/GaN epilayers studied by means of UV Raman scattering. <i>Physica Status Solidi (B): Basic Research</i> , 2008 , 245, 731-734	1.3	5
139	Growth of GaN by metal organic vapor phase epitaxy on ZnO-buffered c-sapphire substrates. <i>Journal of Crystal Growth</i> , 2008 , 310, 944-947	1.6	27
138	Micro-Raman for compositions characterization of selective area growth of Al _x Ga _{1-x} In _{1-x-y} As materials by metal-organic vapor-phase epitaxy. <i>Journal of Crystal Growth</i> , 2008 , 310, 4741-4746	1.6	3
137	MOVPE growth of transition-metal-doped GaN and ZnO for spintronic applications. <i>Journal of Crystal Growth</i> , 2008 , 310, 5032-5038	1.6	26
136	Effects of N doping on ZnO thin films grown by MOVPE. <i>Journal of Crystal Growth</i> , 2008 , 310, 5011-5015	1.6	6
135	Effect of boron incorporation on growth behavior of B _x GaN/GaN by MOVPE. <i>Journal of Crystal Growth</i> , 2008 , 310, 5058-5062	1.6	22
134	AlGa _x N/AlN multiple quantum wells grown by MOVPE on AlN templates using nitrogen as a carrier gas. <i>Journal of Crystal Growth</i> , 2008 , 310, 4927-4931	1.6	5
133	Residual stress relaxation in GaN/sapphire circular pillars measured by Raman scattering spectroscopy. <i>Journal of Crystal Growth</i> , 2008 , 310, 5321-5326	1.6	5
132	Use of ZnO thin films as sacrificial templates for metal organic vapor phase epitaxy and chemical lift-off of GaN. <i>Applied Physics Letters</i> , 2007 , 91, 071120	3.4	81
131	Modeling and characterization of AlGaInAs and related materials using selective area growth by metal-organic vapor-phase epitaxy. <i>Journal of Crystal Growth</i> , 2007 , 298, 28-31	1.6	30
130	GaN materials growth by MOVPE in a new-design reactor using DMHy and NH ₃ . <i>Journal of Crystal Growth</i> , 2007 , 298, 428-432	1.6	40
129	B _x GaN materials on GaN/sapphire substrate by MOVPE using N ₂ carrier gas. <i>Journal of Crystal Growth</i> , 2007 , 298, 316-319	1.6	34
128	Progress on new wide bandgap materials B _x GaN, B _x GaAlN and their potential applications 2007 , 6479, 249		1
127	Low temperature homoepitaxy of GaN by LP-MOVPE using Dimethylhydrazine and nitrogen. <i>Superlattices and Microstructures</i> , 2006 , 40, 476-482	2.8	12

126	Synchrotron high angular resolution microdiffraction analysis of selective area grown optoelectronic waveguide arrays. <i>Journal Physics D: Applied Physics</i> , 2006 , 39, 1422-1426	3	10
125	Microbeam high angular resolution x-ray diffraction in InGaN/GaN selective-area-grown ridge structures. <i>Applied Physics Letters</i> , 2006 , 89, 181926	3.4	16
124	Strain relaxation and surface migration effects in InGaAlAs and InGaAsP selective-area-grown ridge waveguides. <i>Applied Physics Letters</i> , 2006 , 88, 081111	3.4	16
123	MOVPE growth study of BxGa(1-x)N on GaN template substrate. <i>Superlattices and Microstructures</i> , 2006 , 40, 233-238	2.8	10
122	Application of X-ray standing wave (XSW) technique for studies of Zn incorporation in InP epilayers. <i>Computational Materials Science</i> , 2005 , 33, 132-135	3.2	
121	Microbeam high-resolution x-ray diffraction in strained InGaAlAs-based multiple quantum well laser structures grown selectively on masked InP substrates. <i>Journal of Applied Physics</i> , 2005 , 97, 063512	2.5	31
120	Microbeam high-resolution diffraction and x-ray standing wave methods applied to semiconductor structures. <i>Journal Physics D: Applied Physics</i> , 2004 , 37, L9-L12	3	11
119	Micro-X-ray fluorescence and micro-photoluminescence in InGaAsP and InGaAs layers obtained by selective area growth. <i>Journal of Crystal Growth</i> , 2003 , 253, 38-45	1.6	8
118	10 Gbit/s transmitter based on directly modulated InGaAlAs laser operating up to 126°C. <i>Electronics Letters</i> , 2003 , 39, 1653	1.1	6
117	Photonic integrated receiver for 40 Gbit/s transmission. <i>Electronics Letters</i> , 2002 , 38, 1196	1.1	17
116	40-Gb/s tandem electroabsorption modulator. <i>IEEE Photonics Technology Letters</i> , 2002 , 14, 27-29	2.2	46
115	(InGa)(NAs)/GaAs structures emitting in 1.6-μm wavelength range. <i>Optical Materials</i> , 2001 , 17, 185-188	3.3	10
114	InGaAsP/AlGaAs multiple-wavelength vertical-cavity lasers and arrays in the 1.5-μm band fabricated by localized wafer fusion technique 2000 , 4068, 2		
113	TEM study of the morphological and compositional instabilities of InGaAsP epitaxial structures. <i>Journal of Crystal Growth</i> , 2000 , 221, 12-19	1.6	14
112	Carbon doping of InAlAs in LP-MOVPE using CBr ₄ . <i>Journal of Crystal Growth</i> , 2000 , 221, 66-69	1.6	11
111	Quantum well bandgap engineering for 1.5 μm telecom applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000 , 74, 66-69	3.1	7
110	Three-waveguide two-grating codirectional coupler for 1.3-/1.3+/1.5 [μm] demultiplexing in transceiver. <i>Electronics Letters</i> , 2000 , 36, 2030	1.1	4
109	Performance comparison of strained InGaNAs/GaAs and InGaAs/GaAs QW laser diodes grown by MOVPE. <i>Electronics Letters</i> , 2000 , 36, 436	1.1	6

108	Step-bunching instability in strained-layer superlattices grown on vicinal substrates. <i>Applied Physics Letters</i> , 2000 , 76, 306-308	3.4	9
107	Accuracy on emitted wavelengths in DFB laser arrays resulting from the longitudinal mode selection mechanism. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2000 , 6, 191-196	3.8	3
106	Room temperature laser operation of bulk InGaAsN/GaAs structures grown by AP-MOVPE using N ₂ as carrier gas. <i>Electronics Letters</i> , 1999 , 35, 474	1.1	6
105	Multiple distributed feedback operation at 1.55 μm with uniform output powers in a single laser diode. <i>Applied Physics Letters</i> , 1999 , 75, 600-602	3.4	7
104	High-Quality InGaAsN Growth by Metalorganic Vapor-Phase Epitaxy Using Nitrogen Carrier Gas and Dimethylhydrazine, Tertiarybutylarsine as Group V Precursors. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, 1019-1021	1.4	16
103	Growth mode and effect of carrier gas on In _{0.53} Ga _{0.47} As/InP surface morphology grown with trimethylarsine and arsine. <i>Applied Surface Science</i> , 1999 , 150, 161-170	6.7	3
102	Surface morphology of InGaAs and InP materials grown with trimethylarsenic and arsine on vicinal InP substrates. <i>Journal of Crystal Growth</i> , 1999 , 197, 755-761	1.6	7
101	Surface morphology, electrical and optical properties of In _{0.53} Ga _{0.47} As/InP grown by metalorganic vapor-phase epitaxy using trimethylarsine and arsine. <i>Journal of Crystal Growth</i> , 1999 , 204, 1-9	1.6	8
100	Agile and fast switching monolithically integrated four wavelength selectable source at 1.55 μm. <i>IEEE Photonics Technology Letters</i> , 1999 , 11, 12-14	2.2	17
99	Wavelength accuracy in distributed phase-shifted DFB lasers. <i>IEEE Photonics Technology Letters</i> , 1999 , 11, 406-408	2.2	4
98	+55°C pulse lasing at 1.56 [micro sign]m of all-monolithic InGaAlAs/InP vertical cavity lasers. <i>Electronics Letters</i> , 1999 , 35, 811	1.1	11
97	Tunable distributed Bragg reflector laser-electroabsorption modulator based on identical active layer monolithic integration approach. <i>Electronics Letters</i> , 1999 , 35, 1637	1.1	2
96	Tunable distributed Bragg reflector laser-electroabsorption modulator based on the identical active layer integration approach. 1999 ,		1
95	Integrated electroabsorption modulators for high speed transmission at 1.55 μm. <i>European Physical Journal Special Topics</i> , 1999 , 09, Pr2-69		2
94	Planar selective regrowth of high resistivity semi-insulating InP(Fe) by LP-MOVPE for buried lasers using TBP. <i>Journal of Crystal Growth</i> , 1998 , 195, 479-484	1.6	1
93	Tandem of electroabsorption modulators integrated with a DFB laser and an optical amplifier for short optical pulse generation and coding. <i>IEE Proceedings: Optoelectronics</i> , 1998 , 145, 198-200		4
92	Low-damage dry-etched grating on an MQW active layer and dislocation-free InP regrowth for 1.55-μm complex-coupled DFB lasers fabrication. <i>IEEE Photonics Technology Letters</i> , 1998 , 10, 1070-1072	2.2	23
91	Optical properties of low band gap GaAs(1-x)Nx layers: Influence of post-growth treatments. <i>Applied Physics Letters</i> , 1998 , 72, 1409-1411	3.4	158

90	High power operation of widely tunable 1.55 [micro sign]m distributed Bragg reflector laser. <i>Electronics Letters</i> , 1997 , 33, 210	1.1	19
89	Tandem of modulators for high on/off pulse generation (85 dB). <i>Electronics Letters</i> , 1997 , 33, 1491	1.1	4
88	1.3 μm strain-compensated InAsP/InGaP electroabsorption modulator structure grown by atmospheric pressure metalorganic vapor epitaxy. <i>Applied Physics Letters</i> , 1997 , 70, 96-98	3.4	17
87	Low-loss hydrogenated buried waveguide coupler integrated with a four-wavelength distributive Bragg reflector laser array on InP. <i>Applied Physics Letters</i> , 1997 , 71, 1750-1752	3.4	6
86	Integrated multiquantum well distributed feedback laser-electroabsorption modulator with a negative chirp for zero bias voltage. <i>Electronics Letters</i> , 1997 , 33, 53	1.1	11
85	InGaP/InAsP MQW complex-coupled DFB taperless laser with large spot size and high coupling efficiency. <i>Electronics Letters</i> , 1997 , 33, 906	1.1	
84	Very low threshold and high power CW operation in 1.55 [micro sign]m gain-coupled DFB lasers with periodically etched quantum wells. <i>Electronics Letters</i> , 1997 , 33, 1881	1.1	17
83	Metal organic vapor phase epitaxy growth of GaAsN on GaAs using dimethylhydrazine and tertiarybutylarsine. <i>Applied Physics Letters</i> , 1997 , 70, 2861-2863	3.4	90
82	20-Gb/s integrated DBR laser-EA modulator by selective area growth for 1.55- μm WDM applications. <i>IEEE Photonics Technology Letters</i> , 1997 , 9, 898-900	2.2	23
81	Lossless InAsP-InGaP modulator at 1.3 μm for optical conversion of radio signals up to 40 GHz. <i>IEEE Photonics Technology Letters</i> , 1997 , 9, 931-933	2.2	4
80	Accurate wavelength spacing from absorption-coupled DFB laser arrays. <i>IEEE Photonics Technology Letters</i> , 1997 , 9, 1316-1318	2.2	6
79	Gain modeling of strained InGaAsP based MQW optical amplifiers. <i>IEEE Photonics Technology Letters</i> , 1997 , 9, 1475-1477	2.2	5
78	Barrier strain influence on the high-speed properties of compressively strained InGaAsP multiquantum-well laser structures. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1997 , 3, 330-335	3.8	8
77	A new tunable laser using a single electroabsorption tuning super structure grating for subnanosecond switching applications. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1997 , 3, 598-606	3.8	5
76	High reliability of high-power and widely tunable 1.55- μm distributed Bragg reflector lasers for WDM applications. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1997 , 3, 607-614	3.8	19
75	Constant output power and low linewidth in a simple wide-tuning DFB laser with multiwavelength grating. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1997 , 3, 628-631	3.8	1
74	Study of growth rate and composition variations in metalorganic vapour phase selective area epitaxy at atmospheric pressure and application to the growth of strained layer DBR lasers. <i>Journal of Crystal Growth</i> , 1997 , 170, 639-644	1.6	11
73	The role of N ₂ and H ₂ as carrier gas on the selective area MOVPE of InP-based heterostructures using TBAs and TBP as group-V sources. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 44, 37-40	3.1	10

72	InAsP/GaInP strained multilayers grown by MOVPE on (001), (113)B and (110) InP substrates: the role of the surface characteristics. <i>Microelectronics Journal</i> , 1997 , 28, 857-863	1.8	2
71	Selective area MOVPE growth of InP, InGaAs and InGaAsP using TBAs and TBP at different growth conditions. <i>Journal of Crystal Growth</i> , 1997 , 170, 645-649	1.6	14
70	1.55 [micro sign]m polarisation insensitive InGaAsP strained MQW optical amplifier integrated with short spot-size converters. <i>Electronics Letters</i> , 1996 , 32, 1403	1.1	9
69	High-speed tandem of MQW modulators for coded pulse generation with 14-dB fiber-to-fiber gain. <i>IEEE Photonics Technology Letters</i> , 1996 , 8, 218-220	2.2	11
68	Submilliwatt optical bistability in wafer fused vertical cavity at 1.55- μ m wavelength. <i>IEEE Photonics Technology Letters</i> , 1996 , 8, 539-541	2.2	9
67	Simple multiwavelength device fabrication technique using a single-grating holographic exposure. <i>IEEE Photonics Technology Letters</i> , 1996 , 8, 867-869	2.2	10
66	Monolithic integration of multiple-quantum-well lasers and modulators for high-speed transmission. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1996 , 2, 326-335	3.8	47
65	Inhibition of thickness variations during growth of InAsP/InGaP and InAsP/InGaAsP multiquantum wells with high compensated strains. <i>Applied Physics Letters</i> , 1996 , 69, 2279-2281	3.4	16
64	1.3 [micro sign]m InGaP/InAsP MQW lasers with large spot-size and low loss fibre chip coupling fabricated by a standard buried heterostructure process. <i>Electronics Letters</i> , 1996 , 32, 1582	1.1	6
63	Superimposed Bragg gratings on semiconductor material. <i>Electronics Letters</i> , 1996 , 32, 1884	1.1	5
62	Trimethylarsenic as an alternative to arsine in the metalorganic vapor phase epitaxy of device quality In _{0.53} Ga _{0.47} As/InP. <i>Applied Physics Letters</i> , 1996 , 69, 209-211	3.4	3
61	Strained InGaAsP/InGaAsP/InAsP multi-quantum well structure for polarization insensitive electroabsorption modulator with high power saturation. <i>Applied Physics Letters</i> , 1996 , 69, 4131-4132	3.4	16
60	Very simple approach for high performance tunable laser realisation. <i>Electronics Letters</i> , 1996 , 32, 2079	1.1	2
59	Experimental Determination of the Intraband Relaxation Time in Strained Quantum Well Lasers 1996 , 591-593		1
58	Cation interdiffusion in InGaAsP/InGaAsP multiple quantum wells with constant P/As ratio. <i>Applied Physics Letters</i> , 1995 , 66, 718-720	3.4	11
57	Optical gain evaluation in GaInAsP quantum-well lasers: A comparison of the different growth techniques. <i>Journal of Applied Physics</i> , 1995 , 77, 821-826	2.5	5
56	Experimental investigation of the relative importance of carrier heating and spectral-hole-burning on nonlinear gain in bulk and strained multi-quantum-well 1.55 μ m lasers. <i>Applied Physics Letters</i> , 1995 , 67, 771-773	3.4	23
55	Controlled disordering of compressively strained InGaAsP multiple quantum wells under SiO:P encapsulant and application to laser-modulator integration. <i>Journal of Applied Physics</i> , 1995 , 78, 5638-5641	2.5	7

54	High temperature characteristic T ₀ and low threshold current density of 1.3 μm InAsP/InGaP/InP compensated strain multiquantum well structure lasers. <i>Electronics Letters</i> , 1995 , 31, 803-805	1.1	21
53	Electroabsorption modulators for high-bit-rate optical communications: a comparison of strained InGaAs/InAlAs and InGaAsP/InGaAsP MQW. <i>Semiconductor Science and Technology</i> , 1995 , 10, 887-901	1.8	34
52	An Optical Study of Interdiffusion in Strained InP-Based Heterostructures. <i>Japanese Journal of Applied Physics</i> , 1995 , 34, 36-41	1.4	3
51	. <i>IEEE Photonics Technology Letters</i> , 1995 , 7, 185-187	2.2	4
50	20 Gbit/s high-performance integrated MQW TANDEM modulators and amplifier for soliton generation and coding. <i>IEEE Photonics Technology Letters</i> , 1995 , 7, 629-631	2.2	12
49	Suppression of fringe diffraction in localized holographic exposure for DFB laser arrays. <i>IEEE Photonics Technology Letters</i> , 1995 , 7, 721-723	2.2	10
48	Polarization-independent filtering in a grating-assisted horizontal directional coupler. <i>IEEE Photonics Technology Letters</i> , 1995 , 7, 780-782	2.2	6
47	Monolithic integration of InGaAsP-InP strained-layer distributed feedback laser and external modulator by selective quantum-well interdiffusion. <i>IEEE Photonics Technology Letters</i> , 1995 , 7, 1016-1018	2.2	24
46	. <i>Journal of Lightwave Technology</i> , 1995 , 13, 1865-1872	4	20
45	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1995 , 1, 371-374	3.8	13
44	Atmospheric pressure MOVPE growth of high performance polarisation insensitive strain compensated MQW InGaAsP/InGaAs optical amplifier. <i>Electronics Letters</i> , 1995 , 31, 1242-1244	1.1	16
43	Horizontal directional coupler filter suitable for integration in a 1.3+/1.3-μm duplexer. <i>Electronics Letters</i> , 1995 , 31, 2002-2003	1.1	
42	High performance strained MQW lasers at 1.3 μm by MOVPE using arsine generator system. <i>Electronics Letters</i> , 1994 , 30, 1681-1682	1.1	0
41	Very simple approach for high performance DFB laser-electroabsorption modulator monolithic integration. <i>Electronics Letters</i> , 1994 , 30, 1980-1981	1.1	34
40	10 Gbit/s high performance MQW tandem modulator for soliton generation and coding. <i>Electronics Letters</i> , 1994 , 30, 1706-1707	1.1	1
39	Investigation of carrier heating and spectral hole burning in semiconductor amplifiers by highly nondegenerate four-wave mixing. <i>Applied Physics Letters</i> , 1994 , 64, 2492-2494	3.4	40
38	Efficient polarization insensitive electroabsorption modulator using strained InGaAsP-based quantum wells. <i>Applied Physics Letters</i> , 1994 , 64, 3530-3532	3.4	14
37	Zero-loss multiple-quantum-well electroabsorption modulator with very low chirp. <i>Applied Physics Letters</i> , 1994 , 64, 954-956	3.4	13

36	Strained multi-quantum well heterostructures for lasers, modulators and integrated optical devices at 1.3 μ m. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1994 , 28, 279-284	3.1	3
35	Monolithic integration of multiple quantum well DFB lasers and electroabsorption modulators. <i>Microelectronics Journal</i> , 1994 , 25, 691-696	1.8	1
34	Mixing properties of a 20-GHz-bandwidth 1.5- μ m MQW DFB laser in Ku and Ka bands. <i>Microwave and Optical Technology Letters</i> , 1994 , 7, 57-60	1.2	2
33	Full polarization insensitivity of a 20 Gb/s strained-MQW electroabsorption modulator. <i>IEEE Photonics Technology Letters</i> , 1994 , 6, 1203-1206	2.2	32
32	Self-induced laterally modulated GaInP/InAsP structure grown by metal-organic vapor-phase epitaxy. <i>Journal of Applied Physics</i> , 1994 , 75, 7881-7883	2.5	49
31	Taper-waveguide integration for polarisation insensitive InP/InGaAsP based optical amplifiers. <i>Electronics Letters</i> , 1994 , 30, 1290-1291	1.1	13
30	Experimental optimisation of MQW electroabsorption modulators with up to 40 GHz bandwidths. <i>Electronics Letters</i> , 1994 , 30, 1347-1348	1.1	29
29	. <i>IEEE Photonics Technology Letters</i> , 1993 , 5, 1288-1290	2.2	64
28	20 GHz bandwidth 1.5 μ m wavelength VUG DFB laser using a zero net strain In _x Ga _{1-x} AsP _y well active structure grown at constant y. <i>Electronics Letters</i> , 1993 , 29, 1290	1.1	19
27	Transform-limited pulses from low chirp DFB lasers with external feedback. <i>Electronics Letters</i> , 1993 , 29, 518	1.1	1
26	10 Gbit/s transmission experiment over 165 km of dispersive fibre using ASK-FSK modulation and direct detection. <i>Electronics Letters</i> , 1993 , 29, 973-975	1.1	7
25	Carrier transport limited bandwidth of 1.55 μ m quantum-well lasers. <i>Applied Physics Letters</i> , 1993 , 62, 52-54	3.4	26
24	10 Gbit/s operation of polarisation insensitive, strained InGaAsP/InGaAsP MQW electroabsorption modulator. <i>Electronics Letters</i> , 1993 , 29, 1201	1.1	12
23	A new organoindium precursor for electronic materials. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1993 , 17, 34-40	3.1	0
22	High-speed InGaAsP/InGaAsP MQW electroabsorption modulator with high optical power handling capacity. <i>Electronics Letters</i> , 1992 , 28, 2157	1.1	4
21	1.55 μ m multi-quantum-well lasers with record performance obtained by atmospheric pressure MOVPE using organometallic phosphorus precursor. <i>Electronics Letters</i> , 1992 , 28, 1078	1.1	19
20	High power operation of phase-shifted DFB lasers with amplitude modulated coupling coefficient. <i>Electronics Letters</i> , 1992 , 28, 1395	1.1	22
19	. <i>IEEE Photonics Technology Letters</i> , 1992 , 4, 720-723	2.2	30

18	. <i>IEEE Photonics Technology Letters</i> , 1992 , 4, 1335-1338	2.2	9
17	Use of high purity trimethylindium-trimethylamine adduct in MOVPE of InP. <i>Journal of Crystal Growth</i> , 1992 , 124, 93-98	1.6	6
16	Highly thermally stable, high-performance InGaAsP: InGaAsP multi-quantum-well structures for optical devices by atmospheric pressure MOVPE. <i>Journal of Crystal Growth</i> , 1992 , 124, 737-740	1.6	47
15	Large-area metal-organic vapour phase epitaxy for optoelectronic integrated circuits and photonics. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1991 , 9, 69-76	3.1	3
14	Low threshold 1.5 μm SCH-MQW lasers by atmospheric pressure MOVPE and direct comparison of low versus atmospheric pressure MOVPE laser growths. <i>Journal of Crystal Growth</i> , 1991 , 107, 761-766	1.6	2
13	Efficient electroabsorption in InGaAsP/InGaAsP MQW optical waveguide. <i>Electronics Letters</i> , 1991 , 27, 1607	1.1	18
12	. <i>IEEE Journal of Quantum Electronics</i> , 1991 , 27, 1794-1797	2	8
11	State of the art 1.3 μm lasers by atmospheric pressure MOVPE using tertiary butylphosphine. <i>Electronics Letters</i> , 1991 , 27, 1005-1006	1.1	14
10	Microfabrication and optical study of reactive ion etched InGaAsP/InP and GaAs/GaAlAs quantum wires. <i>Applied Physics Letters</i> , 1990 , 56, 830-832	3.4	52
9	Very uniform epitaxy. <i>Progress in Crystal Growth and Characterization</i> , 1989 , 19, 39-49		12
8	Extremely uniform, reproducible growth of device quality InGaAsP:InP heterostructures in the T-shaped reactor at atmospheric pressure. <i>Journal of Crystal Growth</i> , 1988 , 93, 235-241	1.6	20
7			1
6	Designing the relative impact of thickness/composition changes in selective area organometallic epitaxy for monolithic integration applications		1
5	Simultaneous demultiplexing and clock recovery of 80 Gb/s OTDM signals using a tandem electro-absorption modulator		6
4	Integrated photonic devices for fiber optic communication systems		1
3	High quality InGaAsN growth by MOVPE using N_2 carrier gas and dimethylhydrazine, tertiarybutylarsine as group V precursors		1
2	Multiple quantum well distributed feedback laser-electroabsorption modulator light source with 36 GHz		2
1	Novel high performance strained layer MQW monolithically integrated DFB laser-electroabsorption modulator using one identical single active layer		1

